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(54) **Title:** OVERLAY TARGET DESIGN FOR IMPROVED TARGET PLACEMENT ACCURACY

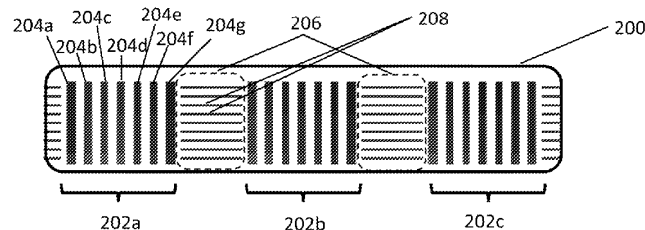


Fig. 3B

(57) **Abstract:** A method for semiconductor metrology includes depositing a first film layer on a semiconductor substrate and a second film layer overlying the first film layer. The first and second film layers are patterned to create an overlay target having a specified geometrical form by using a projection system having a predefined resolution limit to project optical radiation onto the semiconductor substrate through at least one mask. The mask contains target features having target feature dimensions no less than the predefined resolution limit in an arrangement corresponding to the specified geometrical form of the overlay target and assist features interleaved with the target features and having at least one assist feature dimension that is less than the predefined resolution limit.



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